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January 2009

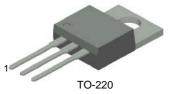
# FJP5200 NPN Epitaxial Silicon Transistor

#### **Applications**

- · High-Fidelity Audio Output Amplifier
- · General Purpose Power Amplifier

#### **Features**

- High Current Capability: I<sub>C</sub> = 17A.
- High Power Dissipation: 80watts.
- High Frequency: 30MHz.
- High Voltage : V<sub>CEO</sub>=250V
- · Wide S.O.A for reliable operation.
- · Excellent Gain Linearity for low THD.
- Complement to FJP1943
- Thermal and electrical Spice models are available.
- · Same transistor is also available in:
  - -- TO264 package, 2SC5200/FJL4315: 150 watts
  - -- TO3P package, 2SC5242/FJA4313: 130 watts
  - -- TO220F package, FJPF5200 : 50 watts



1.Base 2.Collector 3.Emitter

### Absolute Maximum Ratings\* Ta = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
BV <sub>CBO</sub>	Collector-Base Voltage	250	V	
BV <sub>CEO</sub>	Collector-Emitter Voltage	250	V	
BV <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current(DC)	17	А	
I <sub>B</sub>	Base Current	1.5	А	
P <sub>D</sub>	Total Device Dissipation(T <sub>C</sub> =25°C) Derate above 25°C	80 0.64	W W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature	- 50 ~ +150	°C	

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Thermal Characteristics\* T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Max.	Units	
$R_{ heta JC}$	Thermal Resistance, Junction to Case	1.25	°C/W	

<sup>\*</sup> Device mounted on minimum pad size

### **h**<sub>FE</sub> Classification

Classification	R	0
h <sub>FE1</sub>	55 ~ 110	80 ~ 160

### **Electrical Characteristics\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =5mA, I <sub>E</sub> =0	250			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, R <sub>BE</sub> =∞	250			<b>V</b>
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =5mA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =230V, I <sub>E</sub> =0			5.0	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_{C}$ =0			5.0	μΑ
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	55		160	
h <sub>FE2</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =7A	35	60		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =8A, I <sub>B</sub> =0.8A		0.4	3.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =7A		1.0	1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =1A		30		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, f=1MHz		200		pF

<sup>\*</sup> Pulse Test: Pulse Widt=20μs, Duty Cycle≤2%

## **Ordering Information**

Part Number	Marking	Package	Packing Method	Remarks
FJP5200RTU	J5200R	TO-220	TUBE	hFE1 R grade
FJP5200OTU	J5200O	TO-220	TUBE	hFE1 O grade

## **Typical Characteristics**

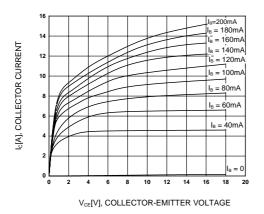


Figure 1. Static Characteristic

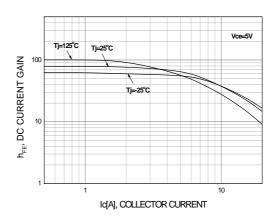


Figure 2. DC current Gain ( R grade )

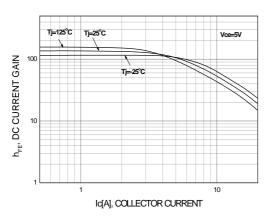


Figure 3. DC current Gain ( O grade )

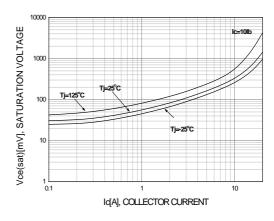


Figure 4. Collector-Emitter Saturation Voltage

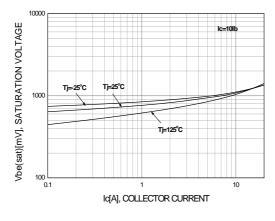


Figure 5. Base-Emitter Saturation Voltage

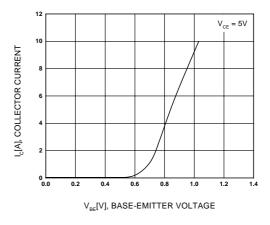


Figure 6. Base-Emitter On Voltage

# **Typical Characteristics**

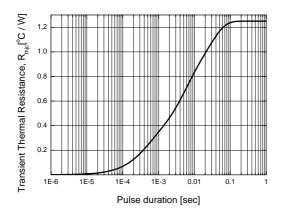


Figure 7. Thermal Resistance

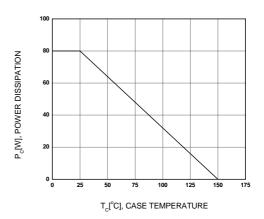
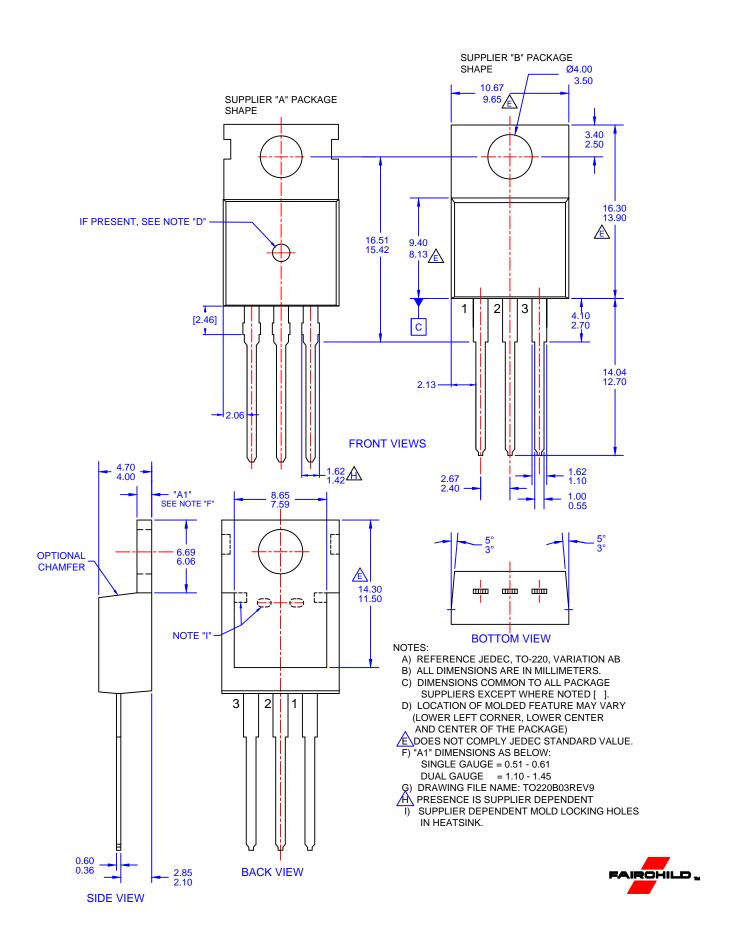


Figure 8. Power Derating



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